# **Driver Transistors**

# **NPN Silicon**

### **Features**

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBTA05L MMBTA06L	V <sub>CEO</sub>	60 80	Vdc
Collector-Base Voltage  MMBTA05L  MMBTA06L	V <sub>CBO</sub>	60 80	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	4.0	Vdc
Collector Current – Continuous	I <sub>C</sub>	500	mAdc
Electrostatic Discharge	ESD	HBM Class 3B MM Class C CDM Class IV	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

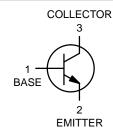
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) T <sub>A</sub> = 25°C	P <sub>D</sub>	225	mW
Derate above 25°C		1.8	mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Derate above 25°C		2.4	mW/°C
Thermal Resistance, Junction–to–Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4  $\times$  0.3  $\times$  0.024 in. 99.5% alumina.



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SOT-23 CASE 318 STYLE 6

### **MARKING DIAGRAMS**





MMBTA05LT1

MMBTA06LT1, SMMBTA06L

1H, 1GM = Specific Device Code

M = Date Code\* ■ Pb–Free Package

(Note: Microdot may be in either location)
\*Date Code orientation and/or overbar may

vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

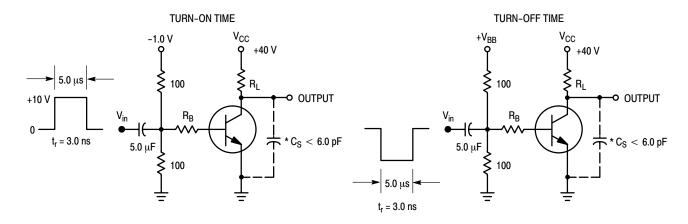
See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS			•		•
Collector – Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	MMBTA05L MMBTA06L	V <sub>(BR)CEO</sub>	60 80	_ _	Vdc
Emitter – Base Breakdown Voltage ( $I_E = 100 \mu Adc, I_C = 0$ )		V <sub>(BR)EBO</sub>	4.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 60 Vdc, I <sub>B</sub> = 0)		I <sub>CES</sub>	-	0.1	μAdc
Collector Cutoff Current ( $V_{CB} = 60 \text{ Vdc}, I_E = 0$ ) ( $V_{CB} = 80 \text{ Vdc}, I_E = 0$ )	MMBTA05L MMBTA06L	I <sub>CBO</sub>	- -	0.1 0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) ( $I_C = 100 \text{ mAdc}$ , $V_{CE} = 1.0 \text{ Vdc}$ )		h <sub>FE</sub>	100 100	_ _	_
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 100 mAdc, I <sub>B</sub> = 10 mAdc)		V <sub>CE(sat)</sub>	-	0.25	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 100 mAdc, V <sub>CE</sub> = 1.0 Vdc)		V <sub>BE(on)</sub>	-	1.2	Vdc
SMALL-SIGNAL CHARACTERISTICS		<u>.</u>			
Current – Gain – Bandwidth Product (Note 4) (I <sub>C</sub> = 10 mA, V <sub>CE</sub> = 2.0 V, f = 100 MHz)		f <sub>T</sub>	100	-	MHz

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>4.</sup>  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.



\*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

<sup>3.</sup> Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

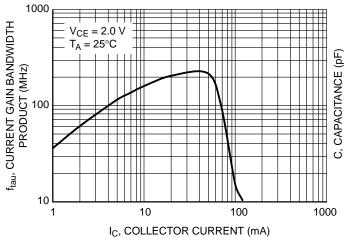


Figure 2. Current Gain Bandwidth Product vs.
Collector Current

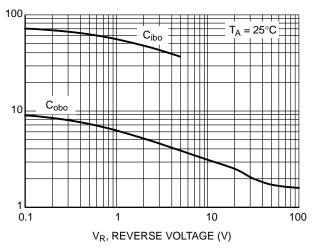


Figure 3. Capacitance

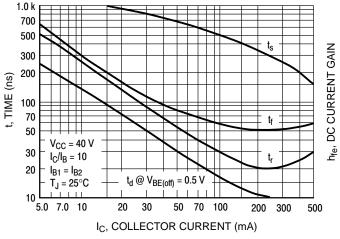


Figure 4. Switching Time

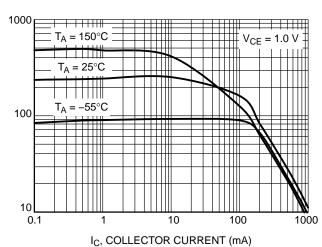


Figure 5. DC Current Gain vs. Collector Current

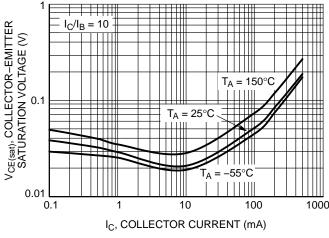


Figure 6. Collector Emitter Saturation Voltage vs. Collector Current

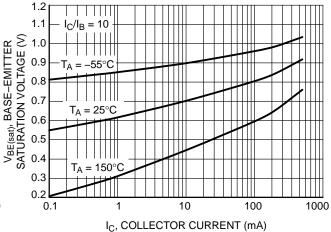


Figure 7. Base Emitter Saturation Voltage vs.
Collector Current

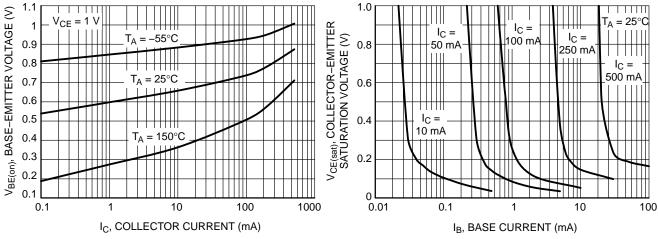


Figure 8. Base Emitter Turn-ON Voltage vs.
Collector Current

Figure 9. Saturation Region

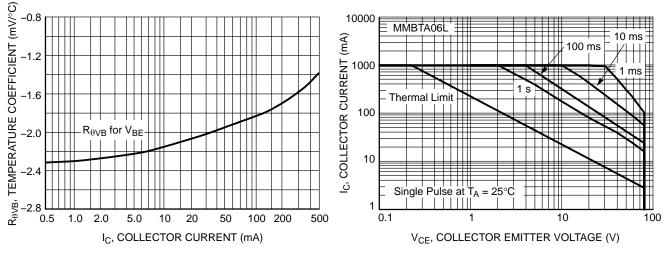


Figure 10. Base–Emitter Temperature Coefficient

Figure 11. Safe Operating Area

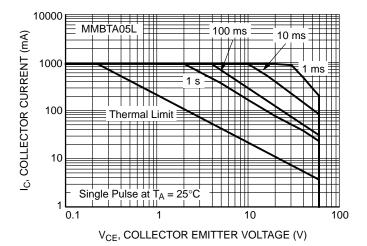


Figure 12. Safe Operating Area

# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MMBTA05LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTA05LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA05LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTA06LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBTA06LT1G*	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTA06LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBTA06LT3G*	SOT-23 (Pb-Free)	10,000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
\*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

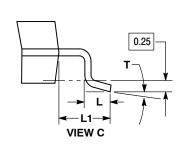


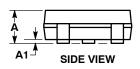
SOT-23 (TO-236) CASE 318-08 **ISSUE AS** 

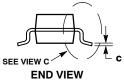
**DATE 30 JAN 2018** 

# SCALE 4:1 D - 3X b

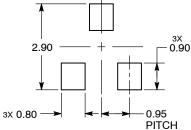
**TOP VIEW** 







#### **RECOMMENDED SOLDERING FOOTPRINT**



DIMENSIONS: MILLIMETERS

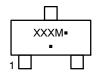
#### NOTES:

- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
  2. CONTROLLING DIMENSION: MILLIMETERS.
  3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH,

	PROT	RUSIONS, OR GATE BURRS.	
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	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

## **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE
OT (1 F O			

SOT-23 (TO-236)

STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
<ol><li>ANODE</li></ol>	<ol><li>SOURCE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. DRAIN	2. GATE
<ol><li>CATHODE</li></ol>	3. GATE	<ol><li>CATHODE-ANODE</li></ol>	<ol><li>ANODE</li></ol>	3. GATE	<ol><li>ANODE</li></ol>

STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>CATHODE</li></ol>	2. ANODE	<ol><li>ANODE</li></ol>
<ol><li>ANODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>CATHODE</li></ol>	<ol><li>ANODE</li></ol>	<ol><li>CATHODE-ANOD</li></ol>	E 3. GATE

STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
<ol><li>SOURCE</li></ol>	<ol><li>OUTPUT</li></ol>	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3 DRAIN	3 INPLIT	3 CATHODE	3. SOURCE	3. GATE	<ol><li>NO CONNECTION</li></ol>

STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE	
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